

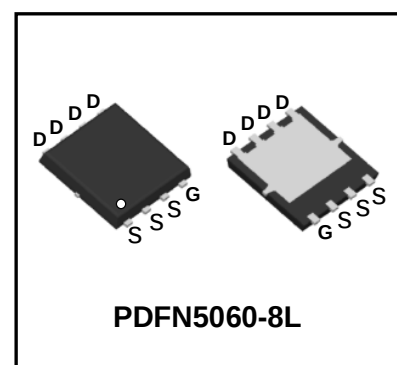
60V N-Channel Enhancement Mode Power MOSFET

Description

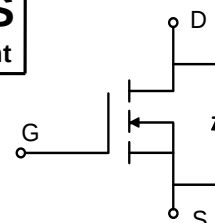
WMB26N06TS uses advanced power trench technology that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

Features

- $V_{DS} = 60V$, $I_D = 26A$
- $R_{DS(on)} < 32m\Omega$ @ $V_{GS} = 10V$
 $R_{DS(on)} < 40m\Omega$ @ $V_{GS} = 4.5V$
- Green Device Available
- 100% EAS Guaranteed
- Optimized for High Speed Smooth Switching



RoHS
compliant



Applications

- Synchronous Rectification
- DC/DC Converter

Absolute Maximum Ratings ($T_c = 25^\circ C$, unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_c = 25^\circ C$	I_D	26	A
	$T_c = 100^\circ C$		16.5	
Pulsed Drain Current ⁴		I_{DM}	104	A
Single Pulse Avalanche Energy ³		EAS	39.2	mJ
Total Power Dissipation	$T_c = 25^\circ C$	P_D	43.8	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient ¹	$R_{\theta JA}$	50	$^\circ C/W$
Thermal Resistance from Junction-to-Case	$R_{\theta JC}$	2.85	$^\circ C/W$

Electrical Characteristics ($T_c = 25^\circ\text{C}$, unless otherwise noted)

Parameter		Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics							
Drain-Source Breakdown Voltage		V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	60	-	-	V
Gate-Body Leakage Current		I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
Zero Gate Voltage Drain Current	T _J =25°C	I _{DSS}	V _{DS} = 60V, V _{GS} = 0V	-	-	1	μA
	T _J =100°C			-	-	100	
Gate-Threshold Voltage		V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.2	1.7	2.5	V
Drain-Source on-Resistance ²		R _{DS(on)}	V _{GS} = 10V, I _D = 10A	-	24	32	mΩ
			V _{GS} = 4.5V, I _D = 5A	-	31.5	40	
Forward Transconductance ²		g _{fs}	V _{DS} = 5V, I _D = 10A	-	15.5	-	S
Dynamic Characteristics							
Input Capacitance		C _{iss}	V _{DS} = 30V, V _{GS} =0V, f =1MHz	-	1355	-	pF
Output Capacitance		C _{oss}		-	60	-	
Reverse Transfer Capacitance		C _{rss}		-	49	-	
Switching Characteristics							
Gate Resistance		R _G	V _{DS} = 0V, V _{GS} =0V, f =1MHz	-	1.2	-	Ω
Total Gate Charge		Q _g	V _{GS} = 10V, V _{DD} = 30V, I _D = 10A	-	22	-	nC
Gate-Source Charge		Q _{gs}		-	4.2	-	
Gate-Drain Charge		Q _{gd}		-	6.9	-	
Turn-on Delay Time		t _{d(on)}	V _{GS} =10V, V _{DD} = 30V,R _G = 3Ω, I _D = 10A	-	6.4	-	ns
Rise Time		t _r		-	15.3	-	
Turn-off Delay Time		t _{d(off)}		-	25	-	
Fall Time		t _f		-	7.6	-	
Drain-Source Body Diode Characteristics							
Diode Forward Voltage ²		V _{SD}	I _S = 10A, V _{GS} = 0V	-	-	1.2	V
Continuous Source Current ^{1,5}		I _S	V _G =V _D =0V , Force Current	-	-	26	A
Reverse Recovery Time		t _{rr}	V _R =30V, I _F =10A, dI _F /dt=100A/μs	-	26	-	ns
Reverse Recovery Charge		Q _{rr}		-	45	-	nC

Notes:

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
2. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. The EAS data shows Max. rating. The test condition is $V_{DD} = 25V, V_{GS} = 10V, L = 0.4mH, I_{AS} = 14A$
4. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)} = 150^\circ\text{C}$.
5. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

Typical Characteristics

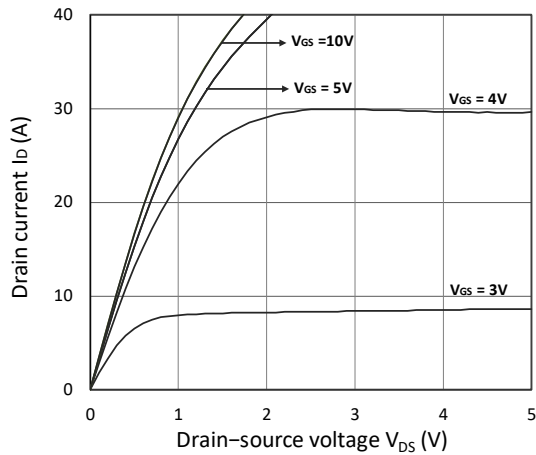


Figure 1. Output Characteristics

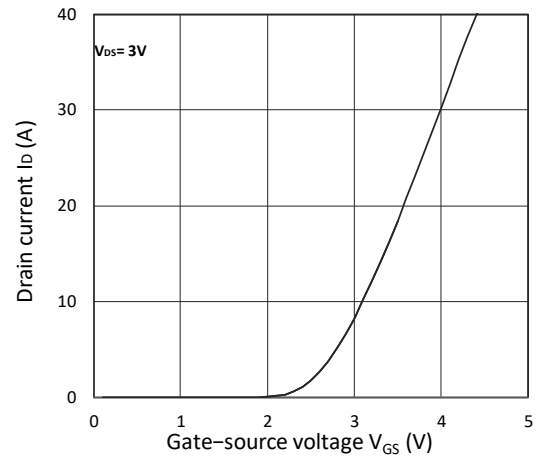


Figure 2. Transfer Characteristics

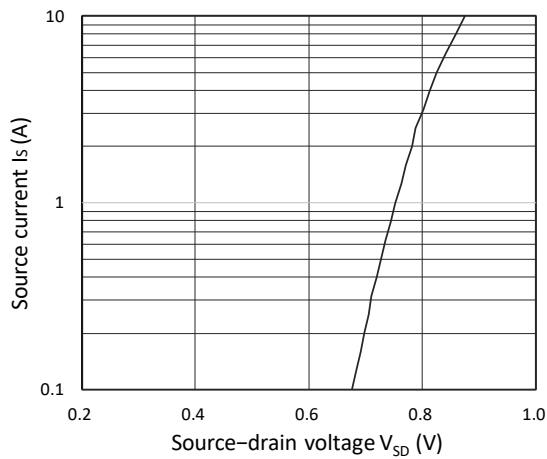
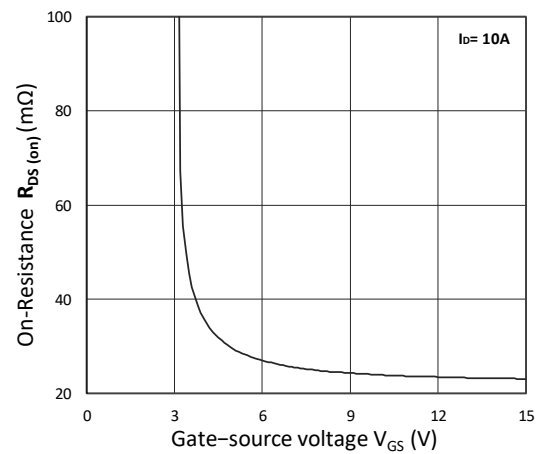
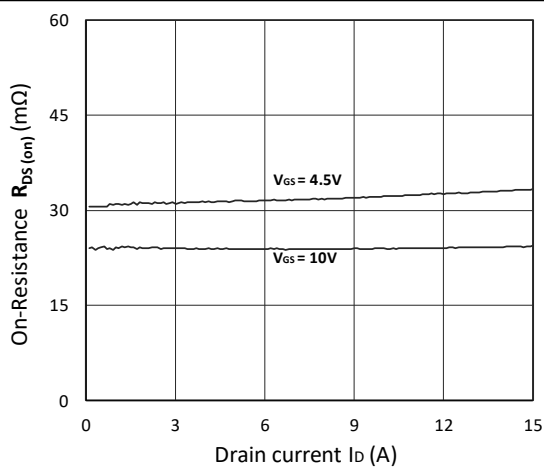
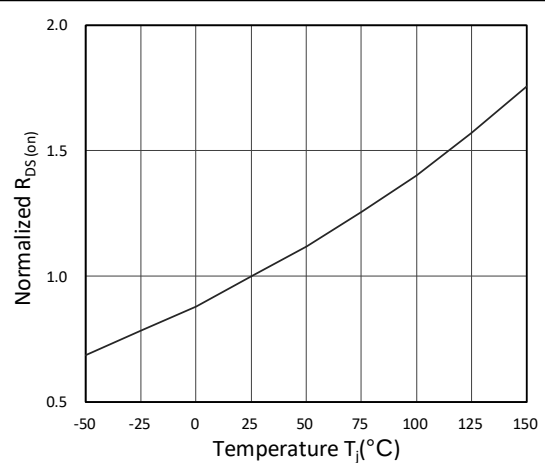


Figure 3. Forward Characteristics of Reverse

Figure 4. $R_{DS(on)}$ vs. V_{GS} Figure 5. $R_{DS(on)}$ vs. I_D Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

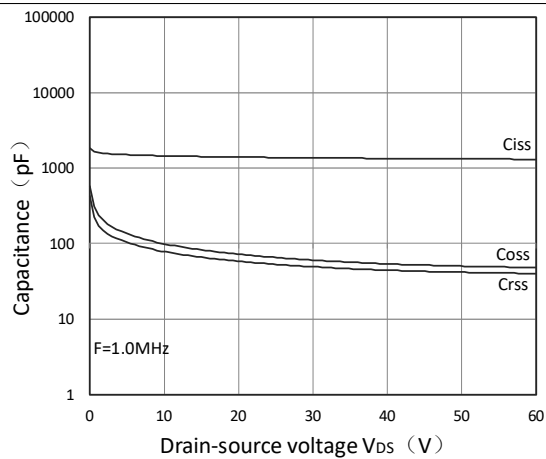


Figure 7. Capacitance Characteristics

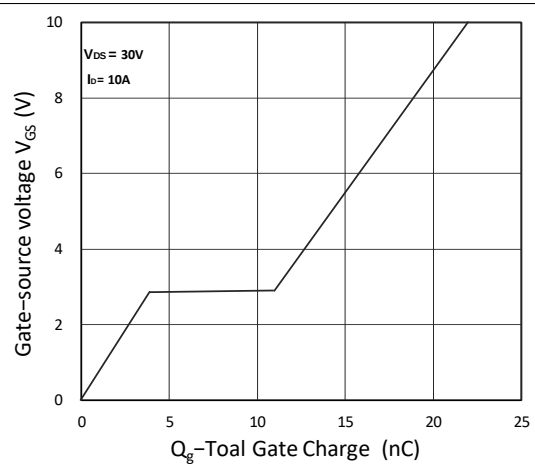


Figure 8. Gate Charge Characteristics

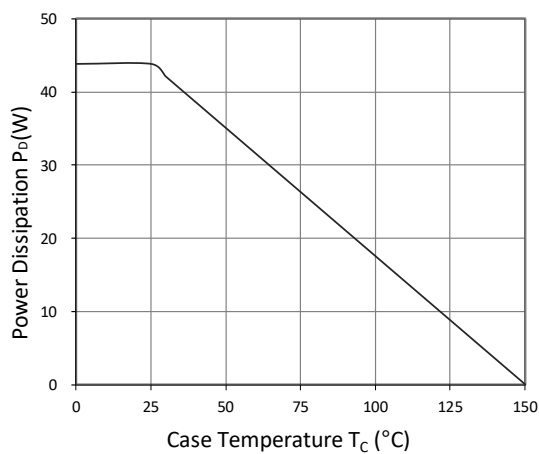


Figure 9. Power Dissipation

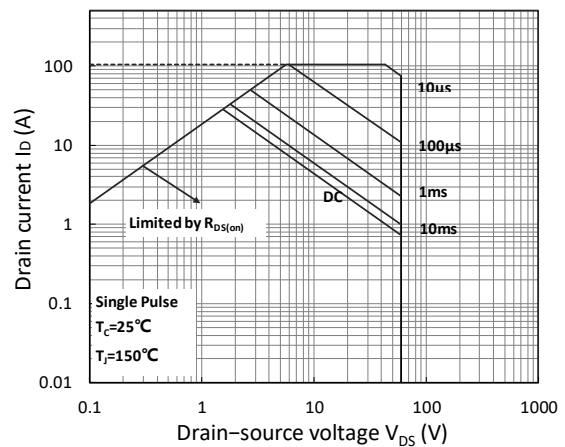


Figure 10. Safe Operating Area

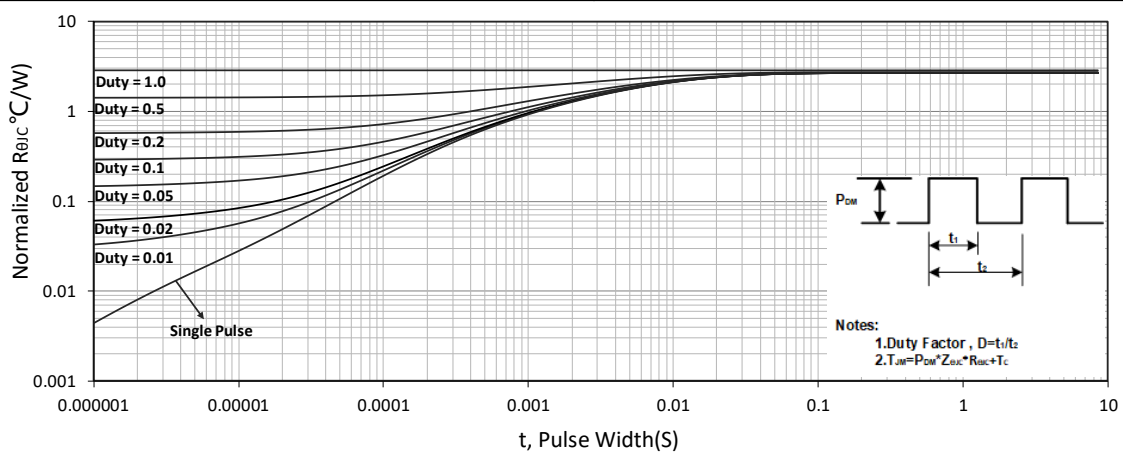


Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuit

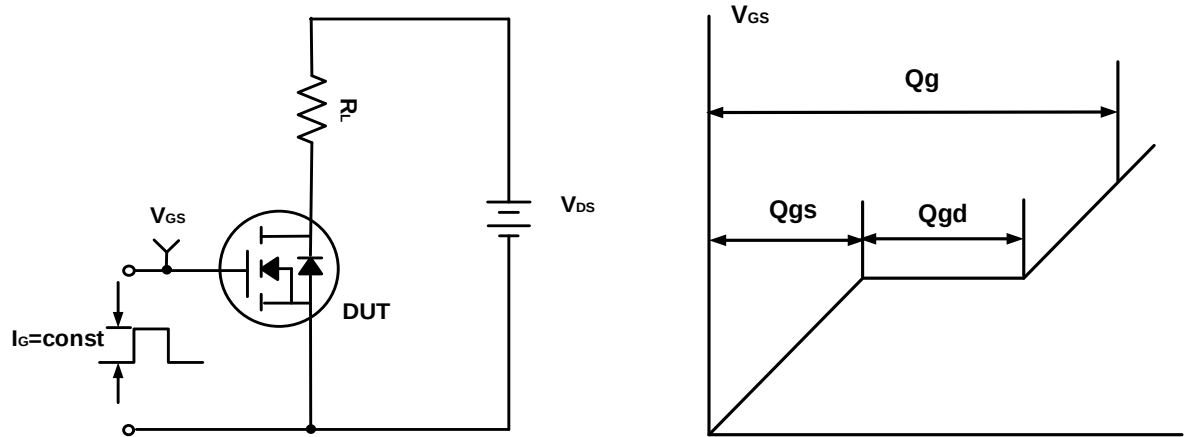


Figure A. Gate Charge Test Circuit & Waveforms

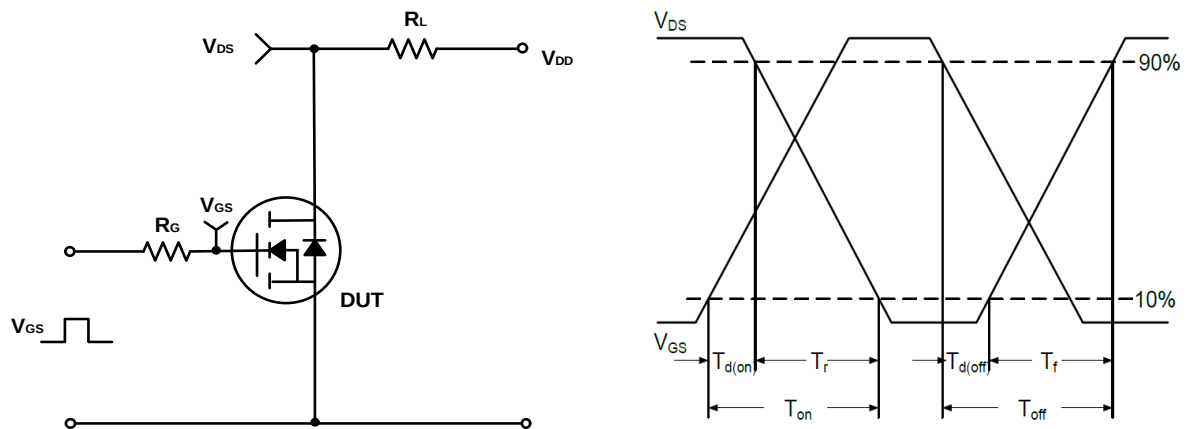


Figure B. Switching Test Circuit & Waveforms

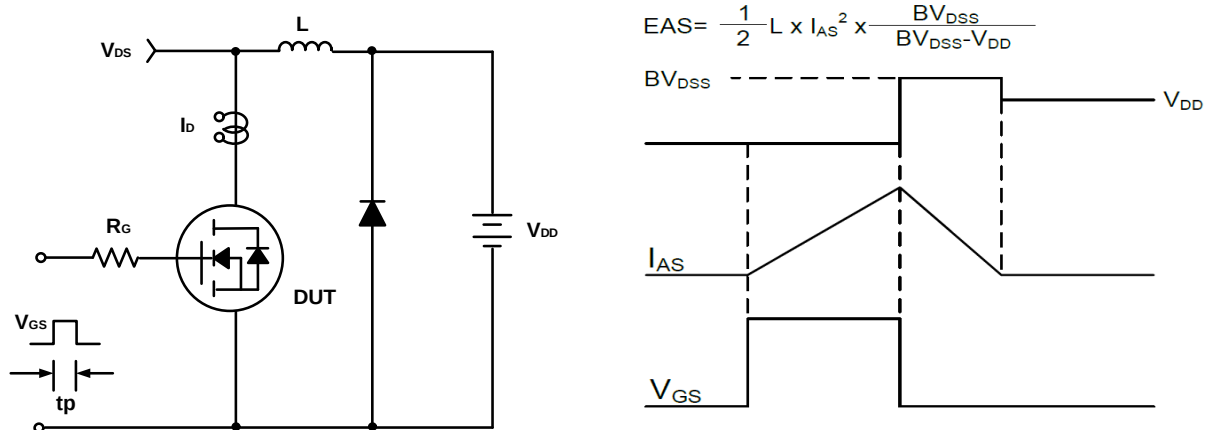
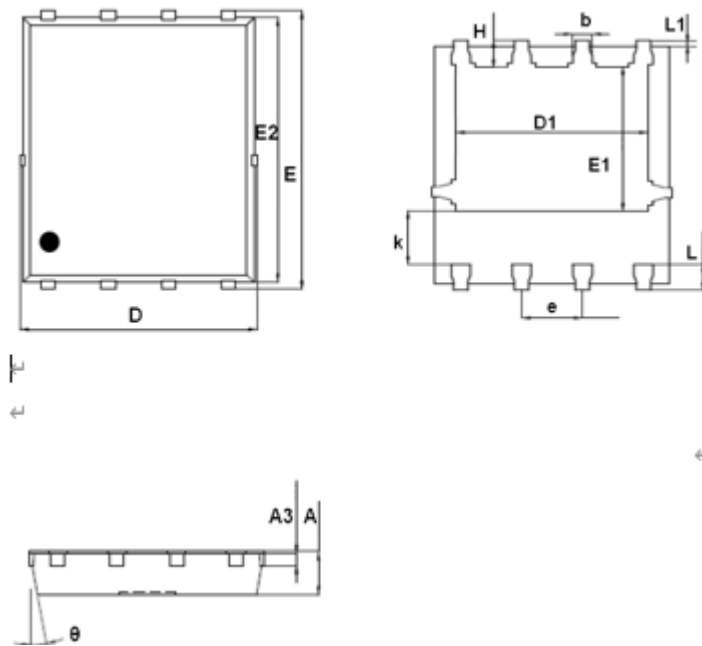


Figure C. Unclamped Inductive Switching Circuit & Waveforms

Mechanical Dimensions for PDFN5060-8L



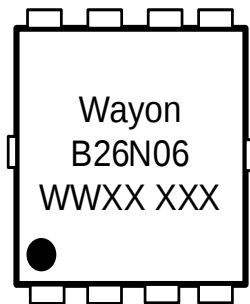
COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	0.9	1.2
A3	0.15	0.35
D	4.8	5.4
E	5.9	6.35
D1	3.61	4.31
E1	3.3	3.92
E2	5.5	6.06
k	1.1	-
b	0.3	0.51
e	1.27BSC	
L	0.38	0.71
L1	0.05	0.36
H	0.38	0.71
Θ	0°	12°

Ordering Information

Part	Package	Marking	Packing method
WMB26N06TS	PDFN5060-8L	B26N06	Tape and Reel

Marking Information



B26N06 = Device code

WWXX XXX= Date code

Contact Information

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